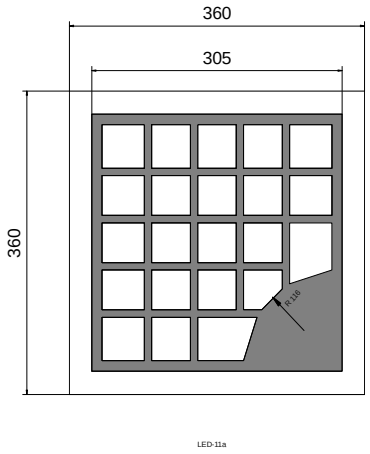
LED - Chip

ELC-1550-17-1

01.07.2011 rev. 04

Radiation	Type	Technology	Electrodes
Infrared	MQW	InGaAs/InP	P (anode) up



typ. dimensions (µm)

typ. thickness
260 µm

anode
gold alloy, 1.5 µm

cathode
gold alloy, 0.5 µm

Maximum Ratings

T_{amb} = 25℃, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			100	mA
Peak forward current	$t_P \leq 50$ µs, $t_P/T = 1/2$	I_{FM}			200	mA

Optical and Electrical Characteristics

T_{amb} = 25℃, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		0.7	0.9	V
Forward voltage	I_F = 100 mA	V_F		0.8	1.0	V
Reverse voltage	I_R = 100 µA	V_R	5			V
Radiant power[1]	I_F = 20 mA	Φ_e	0.55	0.75		mW
Radiant power[1]	I_F = 100 mA	Φ_e	1.7	2.5		mW
Radiant power[2]	I_F = 100 mA	Φ_e		5.0		mW
Peak wavelength	I_F = 20 mA	λ_p	1510	1550	1590	nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$		130		nm
Switching time	I_F = 20 mA	t_r; t_f		25; 45		ns

[1]Measured on bare chip on TO-18 header with JENOPTIK Polymer Systems equipment
[2]Measured on epoxy covered chip on TO-18 header with JENOPTIK Polymer Systems equipment

Labeling

Type	Lot N°	Φ_e(typ) [mW]	V_F(typ) [V]	λ_p(typ) [nm]	Quantity
ELC-1550-17-1		20 mA	20 mA		

Packing: Chips on adhesive film with wire-bond side on top

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